Ambipolar Charge Transport of PCNTC-O and PCNTC-R Cocrystals Obtained Under 1:2 and 1:1 Ratios of Donor and Acceptor

Junle Ren\textsuperscript{1,2}, Zhelin Ding\textsuperscript{1,2}, Yuyao Li\textsuperscript{1,2}, Qiqi Mu\textsuperscript{1,2}, Qiguang Shen\textsuperscript{1,2}, Shoufeng Zhang\textsuperscript{1,*} and Li Zhang\textsuperscript{1,*}

\textsuperscript{1}School of Electronic Engineering, Guangxi University of Science and Technology, Liuzhou 545000, Guangxi, China
\textsuperscript{2}School of Automation, Guangxi University of Science and Technology, Liuzhou 545000, Guangxi, China

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Abstract:

The efficiency of microelectronic devices depends greatly on the charge transport performance of organic semiconductors. The purpose of this work is to analyze the effect of donor-acceptor (D-A) cocrystals on the charge transport characteristics of organic semiconductors using the Marcus theory of electron transfer combined with kinetic Monte Carlo simulations. For two different cocrystals, sesquikis (benzene-1,2,4,5-tetracarbonitrile)-2-(1,3-benzothiazol-2-yl)-3-(pyren-1-yl)prop-2-enenitrile(PCNTC-O) and ben-zene-1,2,4,5-tetracarbonitrile 2-(1,3-benzothiazol-2-yl)-3-(pyren-1-yl)pr-op-2-enenitrile(PCNTC-R) cocrystals, were investigated using 2-(benzo[d]thiazol-2-yl)-3-(pyren-1-yl)acrylonitrile (Py-BZTCN) as the donor and 1,2,4,5-tetracyanobenzene (TCNB) as the acceptor mixed at 1:2 and 1:1 ratios, respectively. According to our calculations, PCNTC-O and PCNTC-R both exhibit bipolar charge transport behaviour with mobilities electron/hole attaining 0.0104/0.1252 and 0.0241/0.0598 cm\textsuperscript{2}/Vs, respectively.

*Corresponding Author
E-mail: zhangsf@gxust.edu.cn, zhangli@gxust.edu.cn

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1. INTRODUCTION

Organic semiconducting materials have attracted a great deal of attention in the last few decades as the basic building block of organic electronic devices. Nowadays, organic light-emitting diodes (OLEDs) [1-4], organic field effect transistors (OFETs) [5-10] and organic photovoltaic (OPVs) [11-15] based on organic semiconductor materials are constantly coming into the limelight, making organic semiconductor materials promising for use in modern microelectronic devices. Improving charge transport in organic semiconductors is thus an important method for improving the efficiency of microelectronics devices.

Organic semiconductors can be classified into unipolar and bipolar materials depending on the type of carrier operation. Unipolar includes p-type where the carriers are holes and n-type where the carriers are electrons. Liu and co-workers reported the presence of 2,6-diphenylanthracene with a mobility of 34 cm²/Vs for p-type organic semiconducting materials [16]. Yamaguchi and co-workers reported S-shaped dinaph-tho[2,1-b;2′,1′-f]thieno[3,2-b]thiophene with a mobility of 11 cm²/Vs [17], both showing excellent hole mobilities. The highest mobility of tetrachlorinated diperylene bisimide has been reported by Lv and co-workers to reach 4.65 cm²/Vs [18] for n-type organic semiconducting materials, Li et al. reported fullerenes with mobility 11 cm²/Vs [19], exhibits good electron mobility.

Compared with unipolar organic semiconductor materials, bipolar organic semiconductor materials have the advantages of simple preparation process, low production cost, low energy consumption, low noise, stable operation and so on, which is why we have to develop bipolar organic semiconductor materials. Huge progress has been made in recent years in the study of organic semiconducting bipolar materials. Compounds synthesized from triphenylamine and pyrimidine-5-carbon-itrile reported by and coworkers have an electron and hole mobilities of 4.4 x 10⁻⁴ and 7.3 x 10⁻³ cm²/Vs, respectively [20]. Currently, donor-acceptor complexes (D-A) have emerged as an efficient way to design and synthesize bipolar charge transport systems. The D-A complexes consisting of the meso-diphenyl tetrathia [22] annulene [2,1,2,1] as the donor molecule and 2,5-difluoro-7,7,8,8-tetracyanoquinodimethane as the acceptor molecule reported by and co-workers were found to have excellent bipolar charge transport with a mobility of 0.47 and 1.57 cm²/Vs for electrons and holes, respectively [21]. In addition, an increasing number of D-A complexes have been reported, showing good bipolar charge transport [22-31].

The charge transport properties of PCNTC-O and PCNTC-R formed from Py-BZTCN as the donor molecule and TCNB as the acceptor molecule were analyzed in a ratio of 1:2 and 1:1 (see Figure 1), which have been synthesized experimentally by Zhang and co-workers [32] and are shown in Table 1. In this work, we have characterized the charge transport performance of PCNTC-O and PCNTC-R in a mechanistic manner using Marcus electron transfer theory combined with kinetic Monte Carlo simulations, the results of our calculations show that PCNTC-O and PCNTC-R both exhibit good bipolar charge transport.

Figure 1: Chemical structures of (a) Py-BZTCN and (b) TCNB, the molecular structure of (c) PCNTC-O and (d) PCNTC-R cocrystals.
2. METHODOLOGY

We have used Marcus electron transfer theory in combination with kinetic Monte Carlo simulations to describe the properties of charge transport in this work. The charge transfer rate equation can be expressed as:

\[ K_{CT} = \frac{1}{\hbar} |V|^2 \left( \frac{\pi e^2}{\Delta G_0} \right) \exp \left( -\frac{\Delta G_0 + \lambda}{4k_B T} \right) \]  

(1)

Here, \( V \) is the electron transfer integral and \( \lambda \) is the reorganization energy resulting from the charge transfer process, \( \Delta G_0 \) is the change in free energy before and after the reaction.

It can be seen that the electron transfer integral and the reorganization energy are two important parameters that determine the charge transfer rate. The direct coupling method for calculating the transfer integral between adjacent molecules can be expressed as:

\[ V_{ij} = \langle \phi_i^0 | f | \phi_j^0 \rangle \]  

(2)

Here, \( f \) is the Fock operator of a pair of molecules, \( \phi_i^0\) and \( \phi_j^0\) are the molecular orbitals of two molecules without perturbation, two orbitals are electron coupled for hole transport when they are HOMO and electron transport when they are LUMO. The transfer integral is closely related to spatial factors such as relative distance and angle between a pair of neighboring molecules, which means that the charge transfer rate is directly related to the molecular stacking mode.

For reorganization energy, there are two methods of calculation, the first is the adiabatic potential energy surface method can be expressed as:

\[ \lambda = \lambda_1 + \lambda_2 \]  

(3)

Where \( \lambda_1 \) is the geometric relaxation energy corresponding to the loss of a hole or electron from the ionic state molecule to the neutral state, and \( \lambda_2 \) is the geometric relaxation energy corresponding to the gain of a hole or electron from the neutral state molecule to the ionic state (see Figure S1). The second is the normal mode method can be expressed as:

\[ \lambda = \sum_j \lambda_j = \sum_j S_j \hbar \omega_j \]  

(4)

Here, \( S_j = \lambda_j / \hbar \omega_j \) is the Huang–Rhys factor, which describes the strength of electron-phonon coupling, \( \omega_j \) is the vibration frequency in the jth normal mode, reorganization energy can be divided into the contribution of each vibration mode.

The charge mobility can be obtained by the Einstein relation:

\[ \mu = \frac{eD}{k_B T} \]  

(5)

Here, \( D \) is the diffusion coefficient of the charge, which can be expressed as:

\[ D = \lim_{t \to \infty} \frac{x(t)^2}{2nt} \]  

(6)

Here, \( x(t) \) is the distance of charge transport, \( t \) is the diffusion time and \( n \) is the dimension of charge transport. The diffusion coefficient can be obtained by a dynamic Monte Carlo simulation process, we arbitrarily choose a molecule as the starting point for a charge that can jump to the nearest surrounding molecule. The probability of following a particular transition path \( j \) can be calculated by \( P_j = k_{CT}^j / \sum_i k_{CT}^i \), the distance of each jump is the central distance between two neighboring molecules, the jump time is \( 1 / k_{CT}^j \). Before each jump of charge, a uniformly distributed random number \( r \) between 0 and 1 is randomly generated, if \( \sum P_{j-1} < r < \sum P_j \), then the charge jumps to the \( j \) molecule, and the corresponding displacement and time are recorded. The diffusion coefficient is obtained by repeating the simulation process, which requires thousands of simulations to obtain a linear relationship between the mean square displacement and the simulation time. Finally, the mobility can be derived from Einstein relation. The calculations using the B3LYP function and the 6-31g* basis group.

3. RESULTS AND DISCUSSION

3.1. Electronic Structure

For PCNTC-O and PCNTC-R cocrystals, we calculated the frontier molecular orbitals using density functional theory (see Figure 2).

From Figure 2, we can see that the highest occupied molecular orbital (HOMO) in the PCNTC-O and PCNTC-R cocrystals is on the Py-BZTCN molecule, while the lowest unoccupied molecular orbital (LUMO) is on the TCNB molecule, indicating a significant charge transfer feature from the Py-BZTCN molecule to the TCNB molecule. For PCNTC-O cocrystal, the calculated energy levels of HOMO and LUMO are -6.03 eV and -3.52 eV, respectively. For PCNTC-R cocrystal, the calculated energy levels of HOMO and LUMO are -5.58 eV and -3.58 eV, respectively. It can be seen that the energy gap of the PCNTC-R cocrystal is narrower than that of the PCNTC-O cocrystal because the Py-BZTCN molecule in the PCNTC-O cocrystal is twisted.
at a larger angle, while the Py-BZTCN molecule in the PCNTC-R cocystal is twisted at a smaller angle and is approximately a plane, so the PCNTC-R cocystal has a better planar molecular skeleton with strong π-π interactions, and the parallel structure can effectively reduce the spatial site resistance, so the energy gap of HOMO-LUMO is reduced.

### 3.2. Reorganization Energy

Reorganization energy is one of the most important factors affecting carrier mobility and in this paper we have calculated the reorganization energy using normal mode analysis. In the PCNTC-O cocystal, the Py-BZTCN molecule electron and hole duschinsky rotation

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**Figure 2:** Electron distribution of the HOMO and LUMO of PCNTC-O and PCNTC-R cocystals.

**Figure 3:** The Py-BZTCN molecule (a) electron and (b) hole duschinsky rotation matrix and TCNB molecule (c) electron and (d) hole duschinsky rotation matrix in PCNTC-O.
matrix and the TCNB molecule electron and hole duschinsky rotation matrix are shown in Figure 3.

In the PCNTC-R cocrystal, the Py-BZTCN molecule electron and hole duschinsky rotation matrix and the TCNB molecule electron and hole duschinsky rotation matrix are shown in Figure 4.

From the duschinsky rotation matrix we can see that Py-BZTCN is discrete while TCNB is linear, so we use the normal mode method to analyze the TCNB molecule reorganization energy.

In the PCNTC-O cocrystal, for the acceptor TCNB, the maximum electron reorganization energy the medium frequency region (see Figure 5), the maximum electron

![Diagram](image_url)

**Figure 4:** The Py-BZTCN molecule (a) electron and (b) hole duschinsky rotation matrix and TCNB molecule (c) electron and (d) hole duschinsky rotation matrix in PCNTC-R.

![Diagram](image_url)

**Figure 5:** The contribution of the TCNB molecule electronic reorganization energy to each vibrational mode in the (a) neutral and (b) anionic states, and contribution of hole reorganization energy to each vibrational mode in the (c) neutral and (d) cationic states in PCNTC-O cocrystal.
The reorganization energy in neutral state reaches 60.24 meV at a frequency of 1568.70 cm\(^{-1}\) and in anionic state reaches 43.32 meV at a frequency of 1484.40 cm\(^{-1}\), this is mainly due to C atoms in the benzene ring from upward and downward motion (the molecular vibration diagram is shown in Figure S2). The maximum hole reorganization energy in the neutral state reaches 37.20 meV at a frequency of 1568.70 cm\(^{-1}\), while in the cationic state the maximum reorganization energy reaches 22.09 meV at frequency of 705.91 cm\(^{-1}\); this is mainly due to the forward and backward motion of the C atom on the TCNB molecule. The large electron reorganization energy of TCNB molecule will have a negative impact on electron mobility.

In the PCNTC-R cocrystal, for the acceptor TCNB, the maximum electron reorganization energy reaches a maximum in the medium frequency region (see Figure 6), the maximum electron reorganization energy in the neutral state reaches 60.26 meV at a frequency of 1567.91 cm\(^{-1}\) and in the anionic state reaches 43.37 meV at a frequency of 1484.23 cm\(^{-1}\), both due to the upward and downward motion of the C atom on the benzene ring (the molecular vibration diagram is shown in Figure S3). The maximum hole reorganization energy in the neutral state reaches 36.13 meV at a frequency of 1567.91 cm\(^{-1}\) and the maximum hole reorganization energy in the cationic state reached 22.11 meV at a frequency of 2313.36 cm\(^{-1}\), this is mainly due to the change of the C atom in the benzene ring from an upward and downward motion to a stretching motion of C and N atoms in cyano, the TCNB molecule reorganization energy calculation results are shown in Table 1.

### 3.3. Transfer Integral

The transfer integral is one of the most important factors affecting carrier mobility. The transfer integral is mainly influenced by spatial factors such as the relative distance and angle between neighbouring molecules, which means that the rate of charge transfer is directly related to the stacking pattern of the molecules. In this work, we have used the direct coupling method for the different paths of PCNTC-O and PCNTC-R cocrystal.
For PCNTC-O cocrystal, we have studied the pathways with neighbouring molecules and the transfer integrals of electrons and holes, centred on the Py-BZTCN molecule, the most important charge hopping pathways given in Figure 7.

The most important transfer integrals of electrons and holes, as well as the intermolecular distances and intermolecular transfer paths are shown in Table 2. Large transfer integrals for hole are path 1 and path 2, this is because they are along the \( \pi \)-stacking direction and these two molecules are in a parallel structure with the central molecule, which can effectively reduce the spatial site resistance and thus can produce a large hole transfer integral. In addition, the path 3 has a large hole transfer integral, as well as the transfer integral of electron reaches a maximum in the path 3, with a maximum value of \(-40.65 \text{ meV}\), this is mainly due to the large overlap of orbitals between the two molecules. In summary, the transfer integral for electrons is higher than holes.

<table>
<thead>
<tr>
<th>Transfer paths</th>
<th>Central distances (Å)</th>
<th>( V'_e \text{(meV)} )</th>
<th>( V'_h \text{(meV)} )</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>4.21</td>
<td>13.92</td>
<td>9.76</td>
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<tr>
<td>2</td>
<td>5.42</td>
<td>8.95</td>
<td>13.66</td>
</tr>
<tr>
<td>3</td>
<td>8.49</td>
<td>-40.65</td>
<td>9.72</td>
</tr>
</tbody>
</table>

Table 2: The Most Important Transfer Integrals of Holes and Electrons in PCNTC-O Cocrystal

Figure 8: The most important charge hopping pathways for hole and electron in PCNTC-R cocrystal.

<table>
<thead>
<tr>
<th>Transfer paths</th>
<th>Central distances (Å)</th>
<th>( V'_e \text{(meV)} )</th>
<th>( V'_h \text{(meV)} )</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>6.11</td>
<td>69.74</td>
<td>1.46</td>
</tr>
<tr>
<td>2</td>
<td>7.31</td>
<td>-56.21</td>
<td>-50.22</td>
</tr>
<tr>
<td>3</td>
<td>7.31</td>
<td>-57.82</td>
<td>5.91</td>
</tr>
</tbody>
</table>

Table 3: The Most Important Transfer Integrals of Holes and Electrons in PCNTC-R Cocrystal
Table 3 shows the most important transfer integrals of electrons and holes in the PCNTC-R cocrystal, the most important charge hopping paths given by Figure 8.

For the PCNTC-R cocrystal, the path 2 has the highest hole transfer integral at -50.222 meV, this path has a larger transfer integral than the other paths, due to the good parallelism and the large overlap area of the orbitals between the two neighbouring molecules. The transfer integrals of the electrons are larger for the paths 1, 2 and 3 and reach a maximum of 69.74 meV for the path 1, this is due to the path 1 has the shortest intermolecular distance and good π-π stacking, thus have a larger transfer integral. For the PCNTC-R cocrystal, the transfer integrals of both holes and electrons reach a relatively large value, which indicates that both holes and electrons have good mobility and therefore the PCNTC-R cocrystal may show a good bipolar transport.

3.4. Anisotropic Property

The anisotropic mobilities of PCNTC-O and PCNTC-R cocrystal have been calculated using kinetic Monte Carlo simulations. Firstly, for the PCNTC-O cocrystal, the electron and hole mobilities were calculated from xy, xz and yz planes, respectively, and the xy plane result are shown in Figure 9 (xz and yz planes see Figure S4). For the electron mobility, there is a maximum on the xy plane along 110° and 290°, and the electron mobility reaches a maximum value of 0.017 cm²/Vs on the xy plane. For the mobility of holes, it can be seen that there is a maximum mobility along 100° and 280° on the xy plane, with the maximum hole mobility reaching a maximum of 0.244 cm²/Vs on the xy plane. As can be seen in Figure 9, the mobility of holes is an order of magnitude higher than that of electrons, although the transport performance for holes is better, but also shows ambipolar charge transport.

For the PCNTC-R cocrystal, we have also calculated the electron and hole mobilities on the xy, xz and yz planes and the xy plane result are shown in Figure 10 (xz and yz planes see Figure S5). Firstly, for the electron mobility, we can see that there is a maximum mobility along 170° and 350° on the xy plane. After our calculations, the electron mobility reaches a maximum value of 0.036 cm²/Vs on the xy plane. For the mobility of holes, it can be seen that there is a maximum mobility along 70° and 250° on the xy plane, with the highest hole mobility reaching 0.119 cm²/Vs on the xy plane.

**Figure 9:** Mobility of electrons in the (a) xy and holes in the (b) xy planes in PCNTC-O cocrystal.

**Figure 10:** Mobility of electrons in the (a) xy and holes in the (b) xy plane in PCNTC-R cocrystal.
plane. As can be seen in Figure 10, the PCNTC-R has a small difference in the mobility of holes and electrons and is able to show a good ambipolar charge transport.

The average carrier mobilities of PCNTC-O and PCNTC-R cocrystals are given in the Table 4. In PCNTC-O cocrystal composed in a 1:2 ratio of donor-acceptor, the average mobilities of electrons and holes is 0.0104 and 0.1252 cm²/Vs respectively. Although the mobility of electrons is an order of magnitude smaller than the mobility of holes, it still shows ambipolar charge transport behavior. Compared to the PCNTC-O cocrystal, in PCNTC-R cocrystal composed in a 1:1 ratio of donor-acceptor, the average mobilities of electrons and holes is 0.0241 and 0.0598 cm²/Vs respectively, which basically achieves a state of balanced electron and hole transport, showing an excellent ambipolar transport, probably because the energy gap in the PCNTC-R cocrystal is smaller than that in the PCNTC-O cocrystal, effectively increasing the carrier mobility.

3.5. Temperature Dependences of the Mobility

In addition, we have analyzed the effect of temperature changes on the mobility of PCNTC-O and PCNTC-R (see Figure 11).

From our calculations, it is clear that the mobility of both PCNTC-O and PCNTC-R increases with increasing temperature due to thermal activation process. As can be seen from Figure 11, the electron mobility of PCNTC-R is higher than that of PCNTC-O as the temperature increases, while the hole mobility of PCNTC-O is higher than that of PCNTC-R. Overall both PCNTC-O and PCNTC-R have higher hole mobilities than electron mobilities.

4. CONCLUSION

In conclusion, we have investigated the PCNTC-O and PCNTC-R cocrystals formed with the donor molecule Py-BZTCN and the acceptor molecule TCNB in the ratios of 1:2 and 1:1. The carrier mobility of PCNTC-O and PCNTC-R cocrystals was calculated using Marcus electron transfer theory combined with kinetic Monte Carlo simulations. We analyzed two important factors affecting carrier mobility, reorganization energy and transfer integral, and found that the reorganization energy of electrons is higher than that of holes in PCNTC-O and PCNTC-R cocrystals, in addition, the transfer integral of PCNTC-R cocrystals is larger than that of PCNTC-O cocrystals from an overall perspective. In conclusion, we have shown that both PCNTC-O and PCNTC-R cocrystals exhibit ambipolar charge transport, compared to the PCNTC-O cocrystal, the And PCNTC-R cocrystal has a more balanced electron and hole mobility, demonstrating excellent charge transport properties of the bipolar type. This is due to the fact that the planarity of PCNTC-R cocrystal composed of 1:1 donor-acceptor is better than that of PCNTC-O cocrystal composed of 1:2 donor-acceptor. To conclude, the relationship between the crystal structure and charge transport has been studied in this
work, which is of great interest in designing high-performance organic devices with ambipolar charge transport.

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SUPPORTING INFORMATION

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REFERENCES


